## Code No: 126EN

# R13

# JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD B.Tech III Year II Semester Examinations, May - 2016

**VLSI DESIGN** 

# (Electronics and Communication Engineering)

# Time: 3 hours

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## Max. Marks: 75

(25 Marks)

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Note: This question paper contains two parts A and B Part A is compulsory which carries 25 marks. Answer all questions in Part A. Part B consists of 5 Units. Answer any one full question from each unit. Each question carries 10 marks and may have a, b, c as sub questions.

		PART -	- A	
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1.a)	Define $g_m$ of MOS transistor.	[2]	
b)	Draw transfer characteristics of CMOS inverter.	[3]	
c)	Define scaling and explain it.	[2]	
d),	Explain difference between stick diagram and layout diagram	[3]	
e):	Define delay and explain different time delays in gate level modeling.	[2]	
·f)	Explain the importance of wiring capacitance of a MOS transistor.	[3]	
g)	Explain the difference between EPROM and EEPROM.	[2]	
h)	Draw 2-bit comparator.	[3]	
i)	Explain difference between PLA and PAL.	[2]	
j)::	Define controllability and observability with respect to testing	[3]	
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#### PART - B

### (50 Marks)

2. Draw the fabrication steps of CMOS transistor and explain its operation in detail. [10]	
3. Draw the fabrication steps of NMOS transistor and explain its operation in detail. [10]	*** * **** *
4.a) Draw the flow chart of VLSI Design flow and explain the operation of each step in detail.	
<ul> <li>b) Draw the stick diagram for three input AND gate. [6+4]</li> <li>5. What is the purpose of design rule? What is the purpose of stick diagram? What are the different approaches for describing the design rule? Give three approaches for making contacts between poly silicon and discussion in NMOS circuit. [10]</li> </ul>	SR
<ul> <li>6.a) Draw and explain fan in and fan out characteristics of different CMOS design in technologies: in technologies:</li></ul>	**** **** **** **** **** **** **** *
7. What are the alternate gate circuits available? Explain any one of item with suitable sketch by taking NAND gate as an example. [10]	
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	8.a) Draw t	he basic circuit	diagram of static	RAM and expla	in its operation.		
	<ul> <li>b): Draw the basic block diagram of 4-bit adder and explain its operation in detail</li></ul>						
4 1 X 4 4 X 4 X 4	10.a) Why th b) What i	ne chip testing is s the drawback	s needed? At what of serial scan? Ho	ow to overcome	chip ean occur? this?	[5+5] [5+5]	
					wer design in detai yzed.	l. [5+5]	
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